ACE4010M200P
P-Channel 100-V MOSFET

Description

The ACE4010M200P uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

Features

- Low r_{DS}(on) trench technology
- Low thermal impedance
- Fast switching speed

PRODUCT SUMMARY		
V_{DS} (V)	r_{DS}(on) (mΩ)	I_D(A)
-100	265 @ V_{GS} = -10V	-27[a]
	280 @ V_{GS} = -5.5V	

Applications

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Absolute Maximum Ratings

Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	-100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[a]	T_A=25℃	I_D	-27	A
Pulsed Drain Current[b]		I_{DM}	-100	A
Continuous Source Current (Diode Conduction)[a]		I_S	100	A
Power Dissipation[a]	T_A=25℃	P_D	300	W
Operating temperature / storage temperature		T_J/T_{STG}	-55~150	℃

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	t <= 10 sec	$R_{θJA}$	62.5	°C/W
	Steady State		1	

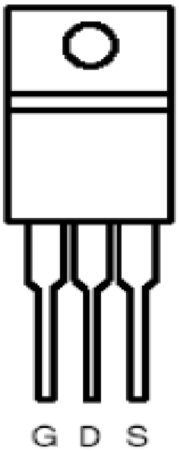
Notes

a. Surface Mounted on 1” x 1” FR4 Board.

b. Pulse width limited by maximum junction temperature

Packaging Type

TO-220



Ordering information

ACE4010M200P XX + H

- Halogen - free
- Pb - free
- ZM：TO-220

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Electrical Characteristics

T_A=25℃ , unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 uA	1			V
Gate-Body Leakage	I_{GSS}	V_{DS}= 0 V, V_{GS}= ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-80 V, V_{GS} = 0 V			-1	uA
		V_{DS} = -80 V, V_{GS} = 0 V, T_J = 55°C			-25	
On-State Drain Current	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = 10 V	100			A
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = -10 V, I_D = 20 A			265	mΩ
		V_{GS} = -5.5 V, I_D = 18 A			280	
Forward Transconductance	g_{fs}	V_{DS} = -15 V, I_D = 20 A		25		S
Diode Forward Voltage	V_{SD}	I_S= -20 A, V_{GS} = 0 V		-1		V
Dynamic						
Total Gate Charge	Q_g	V_{DS}= -50 V, V_{GS} = -5.5 V, I_D= -10 A		22		nC
Gate-Source Charge	Q_{gs}			8.2		
Gate-Drain Charge	Q_{gd}			8.8		
Turn-On Delay Time	$t_{d(on)}$	V_{DS}= -50 V, R_L= 5 Ω, I_D = -10 A, V_{GEN}= -10 V, R_{GEN}= 6 Ω		8		ns
Rise Time	t_r			7		
Turn-Off Delay Time	$t_{d(off)}$			39		
Fall Time	t_f			26		
Input Capacitance	C_{iss}	V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz		1615		pF
Output Capacitance	C_{oss}			107		
Reverse Transfer Capacitance	C_{rss}			87		

Note :

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing

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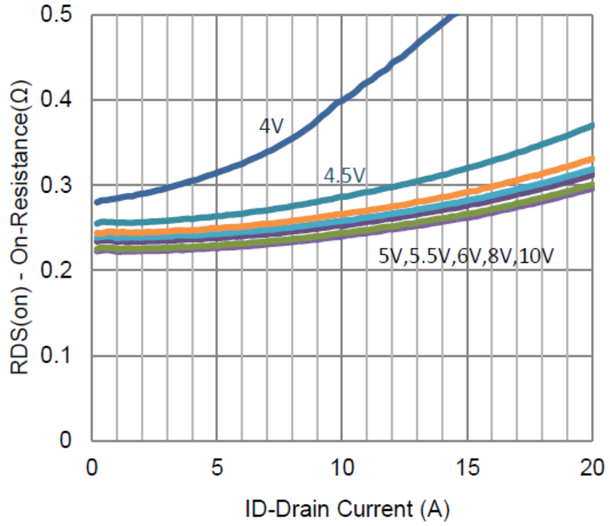
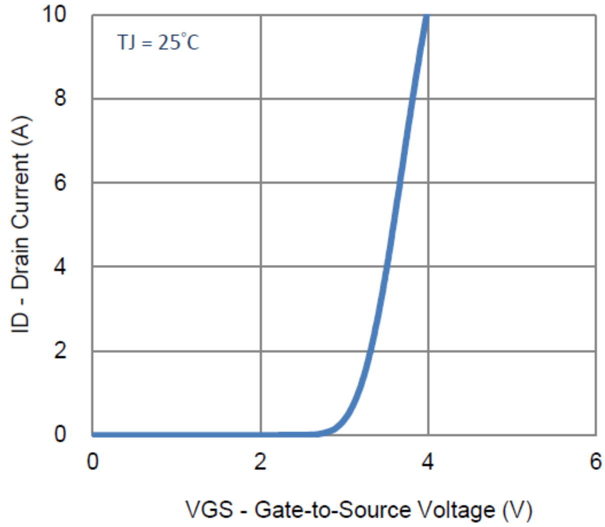
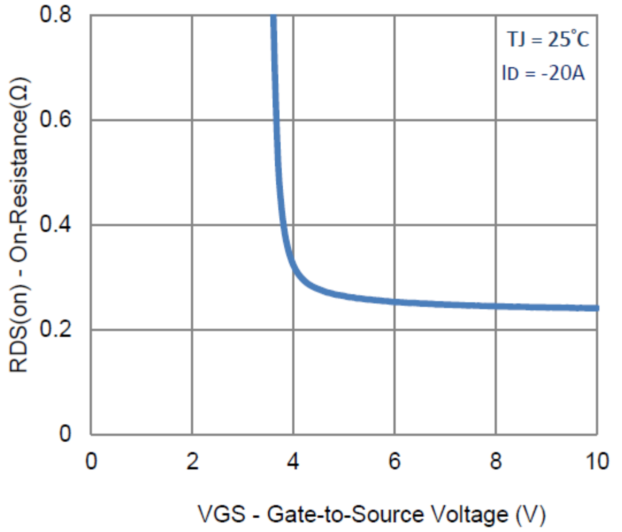
Typical Performance Characteristics



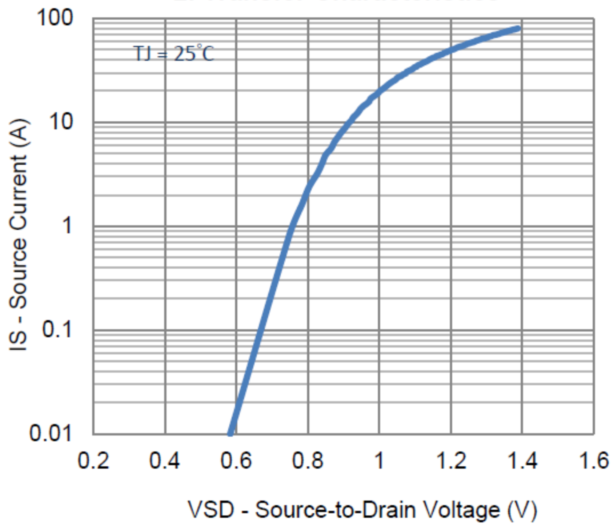
1. On-Resistance vs. Drain Current



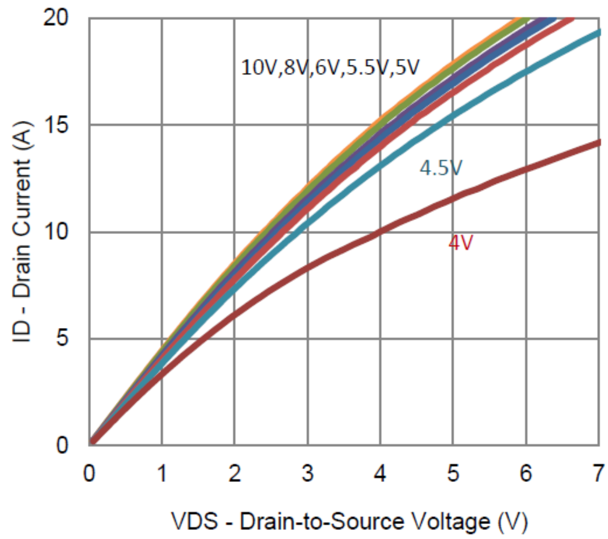
2. Transfer Characteristics



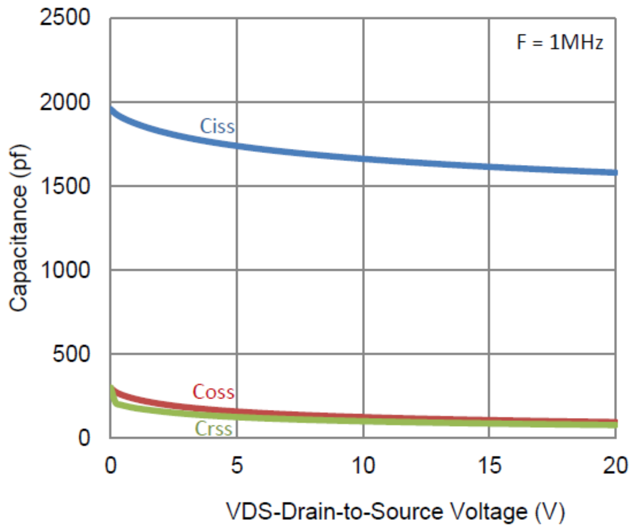
3. On-Resistance vs. Gate-to-Source Voltage



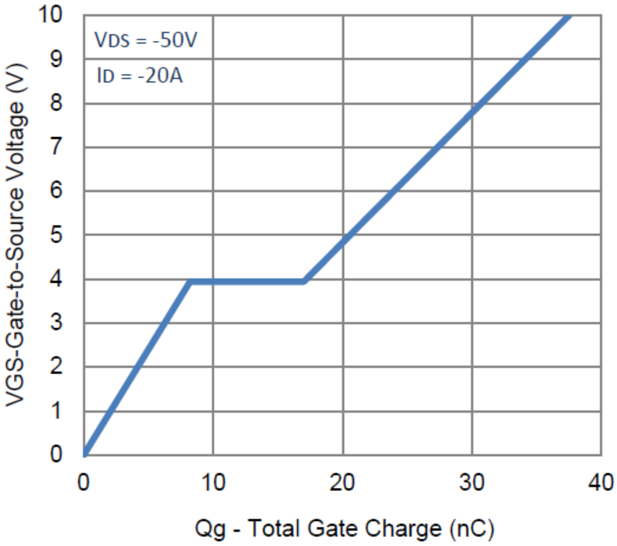
4. Drain-to-Source Forward Voltage



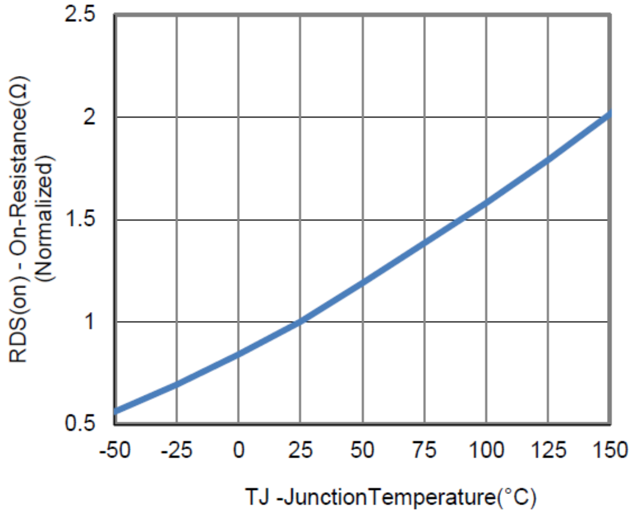
5. Output Characteristics



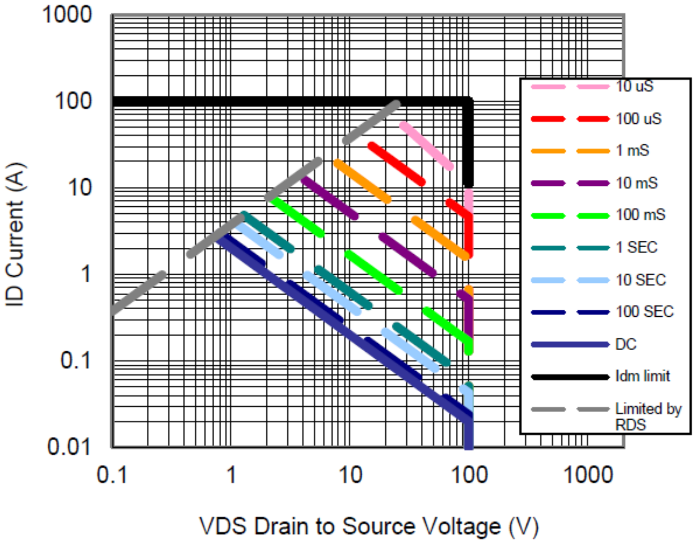
6. Capacitance



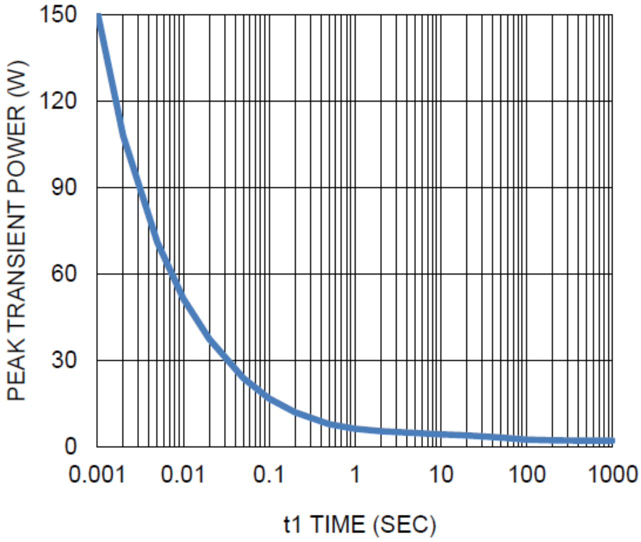
7. Gate Charge



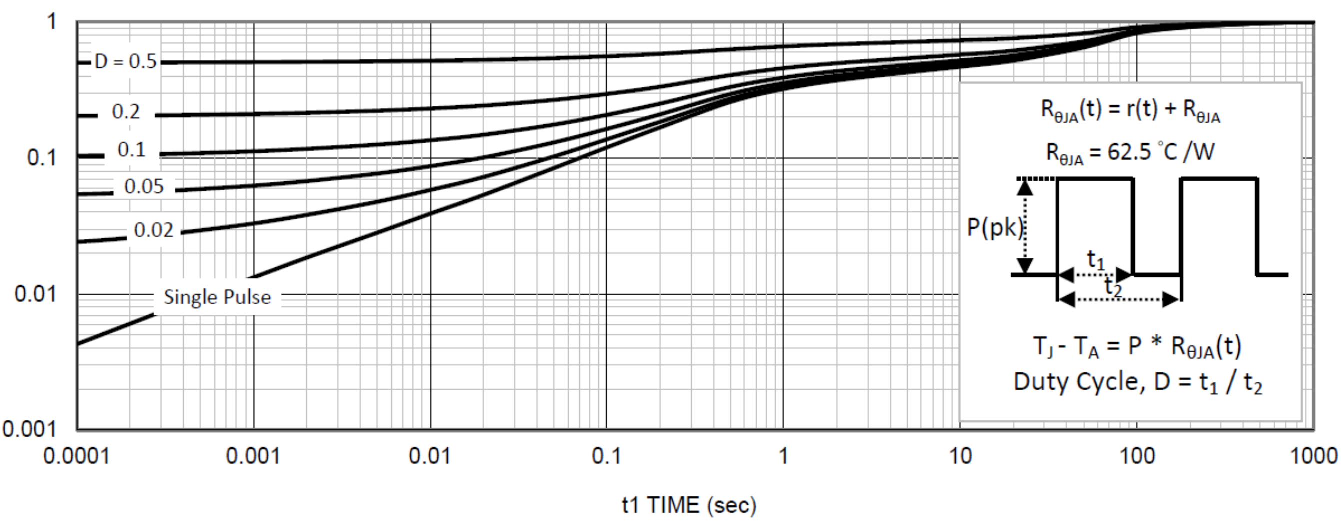
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

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Packing Information

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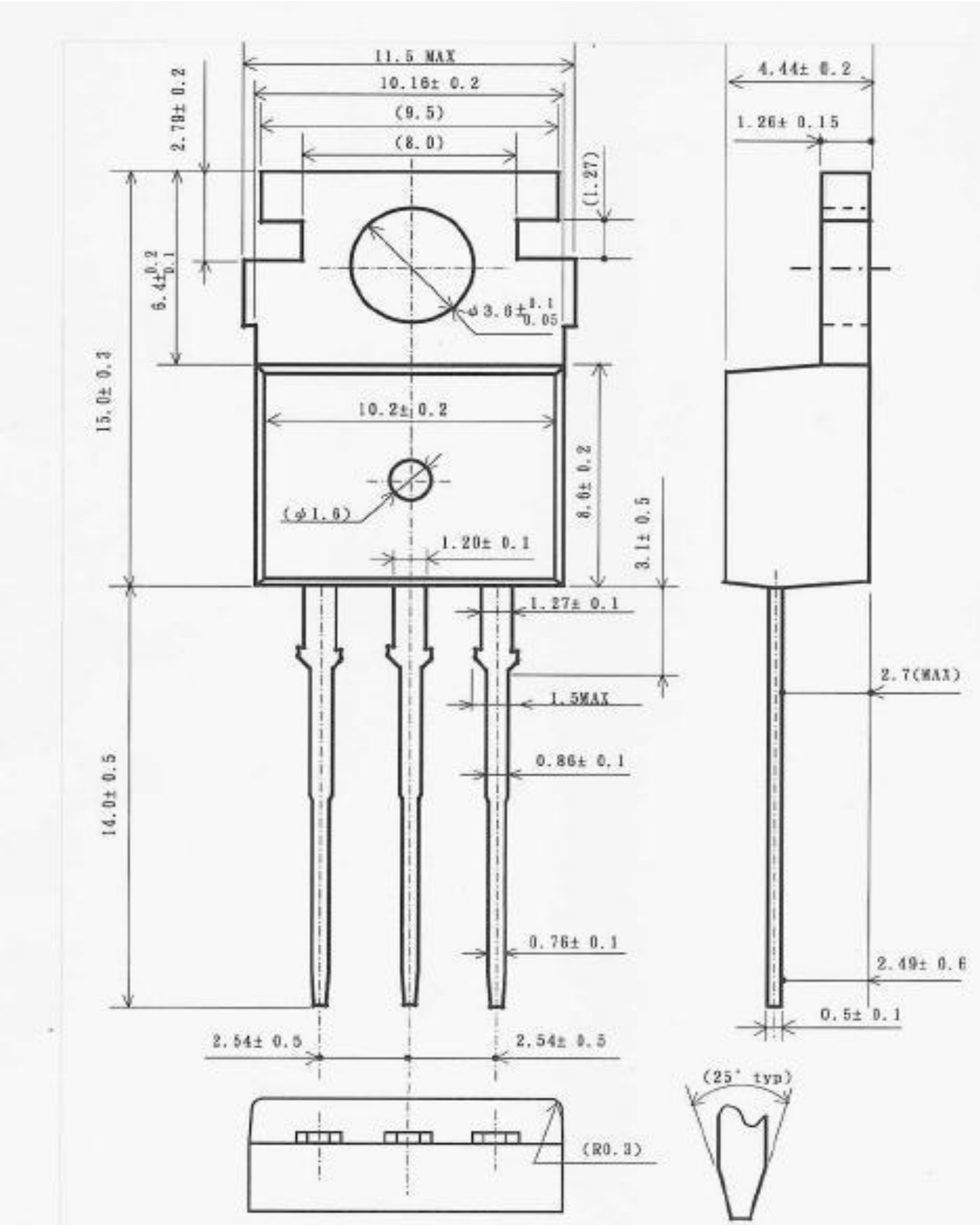

Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and shoes failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.